

Features

- Super Junction High Voltage MOSFET technology
- High Density Cell Design For Low $R_{DS(on)}$
- Moisture Sensitivity Level 1
- Halogen Free "Green" Device^(Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

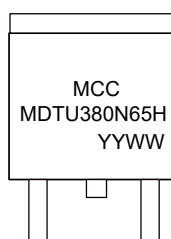
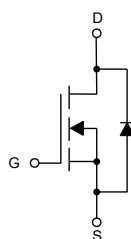
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 48°C/W Junction to Ambient^(Note2)
- Thermal Resistance: 1.7°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current	I_D	8.7	A
		5.5	
Pulsed Drain Current ^(Note 3)	I_{DM}	34.8	A
Total Power Dissipation ^(Note 4)	P_D	73	W
Single Pulsed Avalanche Energy ^(Note 5)	E_{AS}	93.75	mJ

Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. $T_J = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$, $R_g = 25\Omega$, $L = 30\text{mH}$.

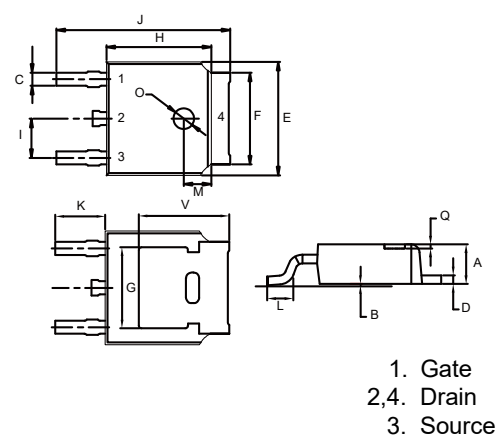
Internal Structure and Marking Code



4 codes in total
YY is the year
WW is the week

N-CHANNEL MOSFET

DPAK(TO-252)



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.087	0.094	2.20	2.40	
B	0.000	0.005	0.00	0.13	
C	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
E	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
H	0.236	0.244	6.00	6.20	
I	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
O	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	650			V
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			1	μA
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.2	3.0	3.8	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5A		300	380	mΩ
Gate Resistance	R _g	f=1 MHz, Open drain		4.0		Ω
Diode Characteristics						
Continuous Body Diode Current	I _S				11	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =8.7A		0.88	1.2	V
Reverse Recovery Time	t _{rr}	I _F =8.5A, dI _F /dt=100A/μs, V _R =325V		208		ns
Reverse Recovery Charge	Q _{rr}			2086		nC
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =325V,V _{GS} =0V,f=1MHz		625		pF
Output Capacitance	C _{oss}			4.7		
Reverse Transfer Capacitance	C _{rss}			1.3		
Total Gate Charge	Q _g	V _{DS} =325V,V _{GS} =10V,I _D =8.5A		13.7		nC
Gate-Source Charge	Q _{gs}			3.0		
Gate-Drain Charge	Q _{gd}			5.7		
Turn-On Delay Time	t _{d(on)}	V _{DD} =325V, V _{GS} =10V, I _{DS} =8.5A,R _{GEN} =3Ω		30		ns
Turn-On Rise Time	t _r			23		
Turn-Off Delay Time	t _{d(off)}			18		
Turn-Off Fall Time	t _f			13		

Curve Characteristics

Fig.1 - Typical Output Characteristics

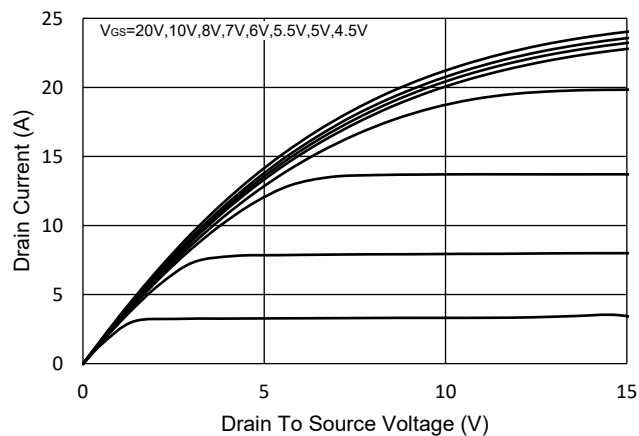


Fig.2 - Transfer Characteristics

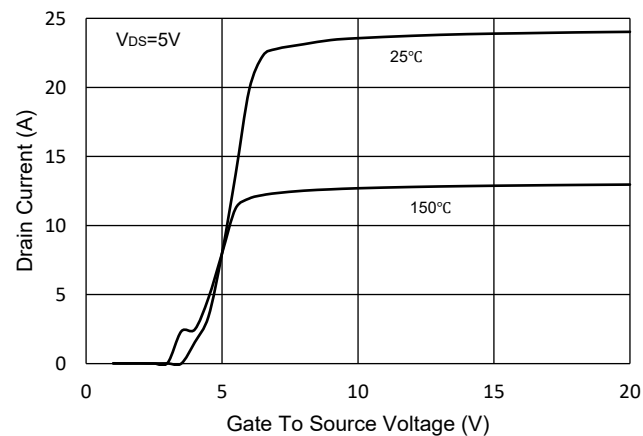


Fig.3 - $R_{DS(ON)}$ - V_{GS}

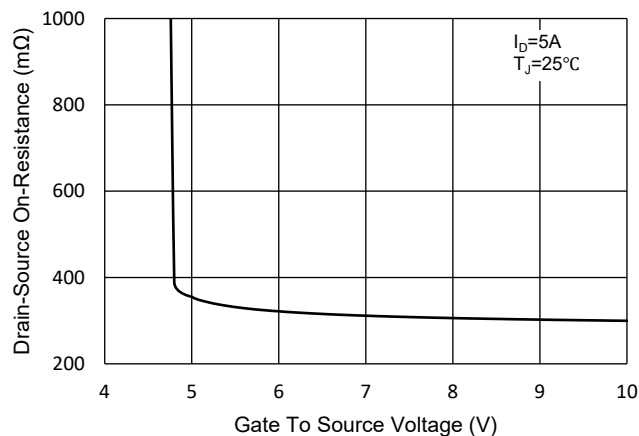


Fig.4 - $R_{DS(ON)}$ - I_D

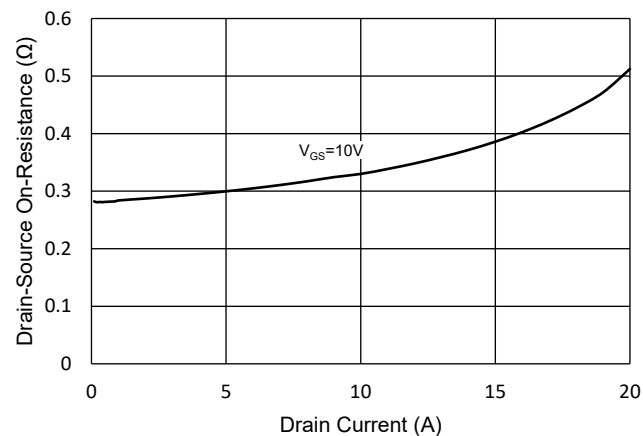


Fig.5 - Capacitance Characteristics

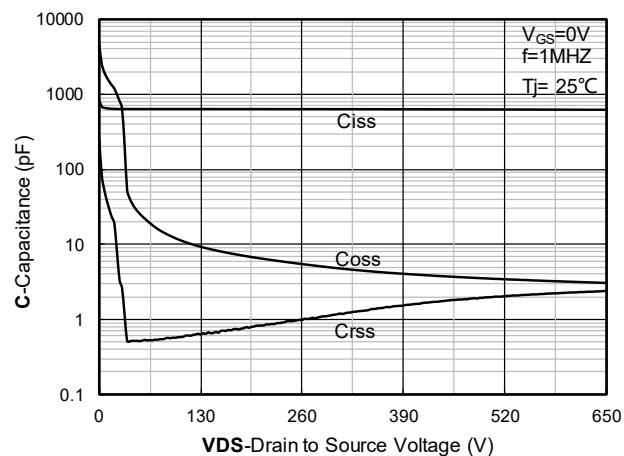
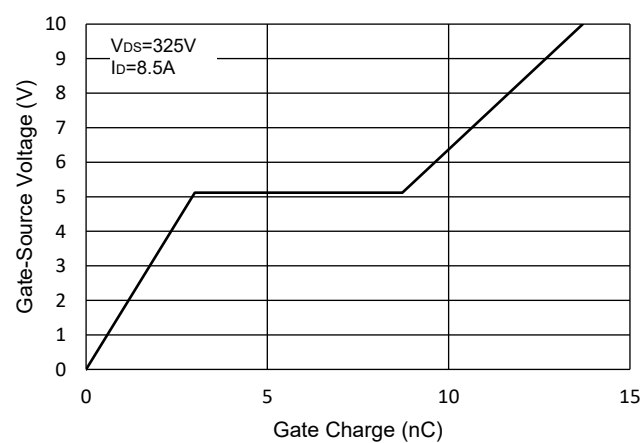


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

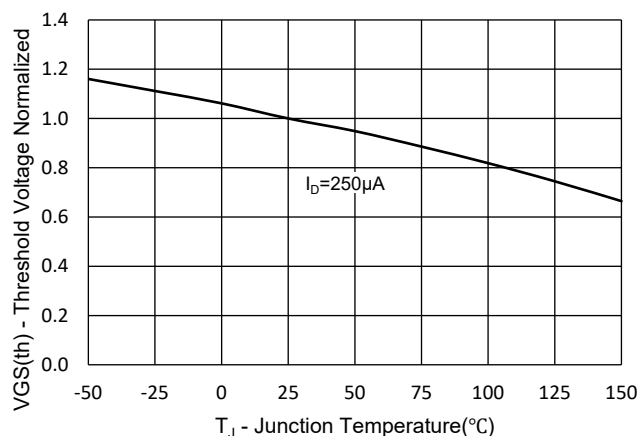


Fig.8 - Normalized On Resistance Characteristics

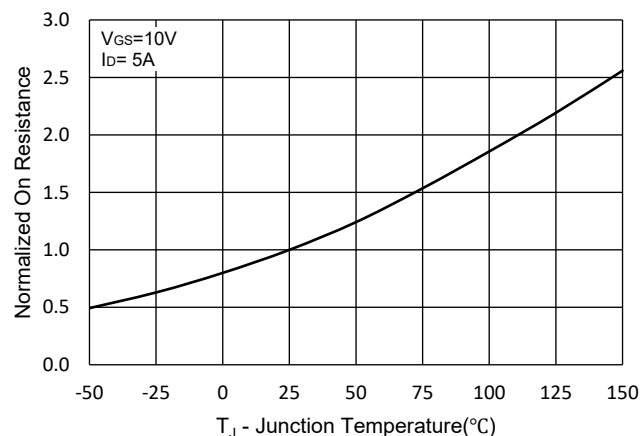


Fig.9 - $I_S - V_{SD}$

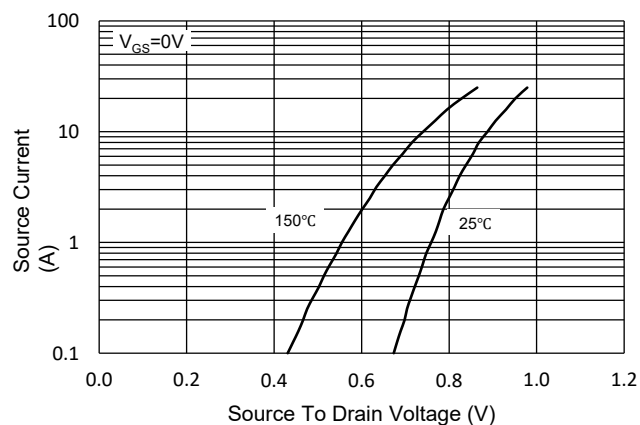


Fig.10 - Drain Current

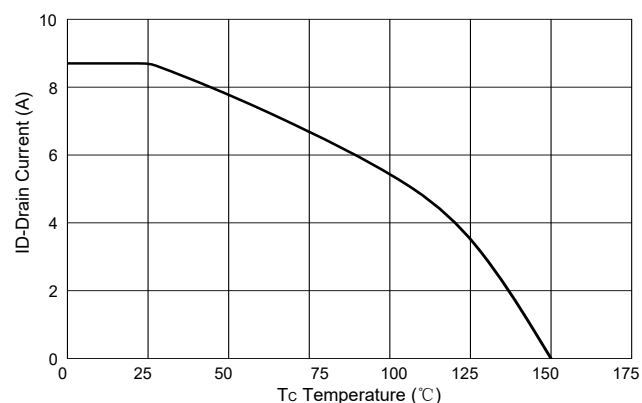
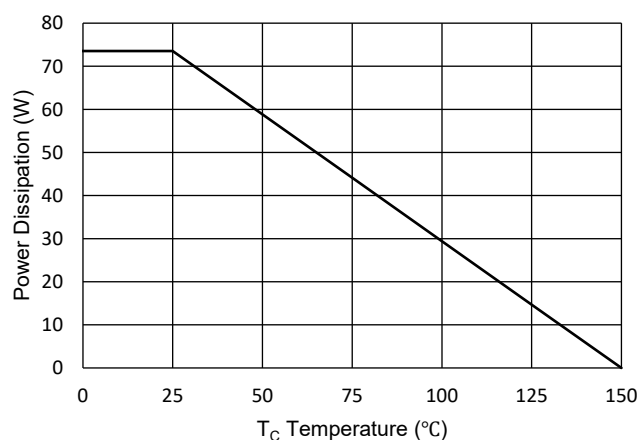


Fig.11 - PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

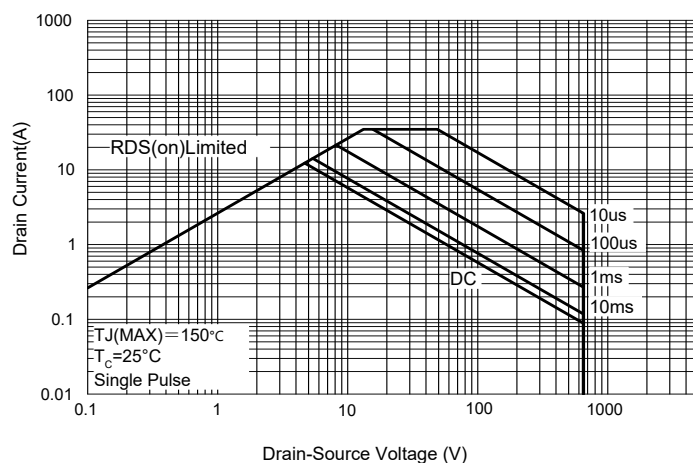
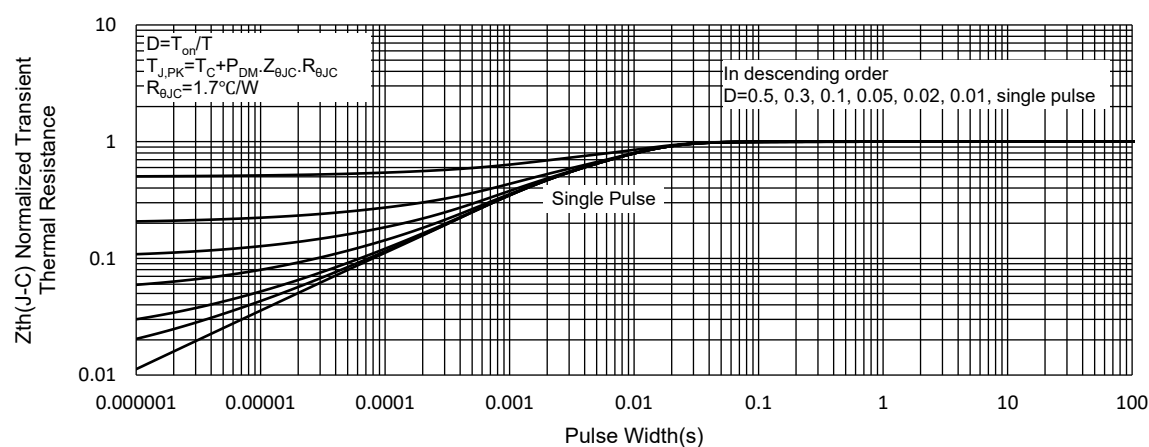


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

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